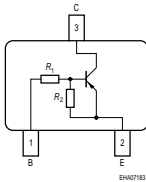


PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1 = 4.7k\Omega$, $R_2 = 4.7k\Omega$)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101


BCR162


Type	Marking	Pin Configuration						Package
		1=B	2=E	2=C	-	-	-	
BCR162	WUs	1=B	2=E	2=C	-	-	-	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	30	
Input reverse voltage	$V_{i(rev)}$	10	
Collector current	I_C	100	mA
Total power dissipation- $T_S \leq 102^\circ\text{C}$	P_{tot}	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 240	K/W

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 10 \text{ V}, I_C = 0$	I_{EBO}	-	-	1.61	mA
DC current gain ²⁾ $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	h_{FE}	20	-	-	-
Collector-emitter saturation voltage ²⁾ $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(off)}$	0.8	-	1.5	
Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0.3 \text{ V}$	$V_{i(on)}$	1	-	2.5	
Input resistor	R_1	3.2	4.7	6.2	k Ω
Resistor ratio	R_1/R_2	0.9	1	1.1	-

AC Characteristics

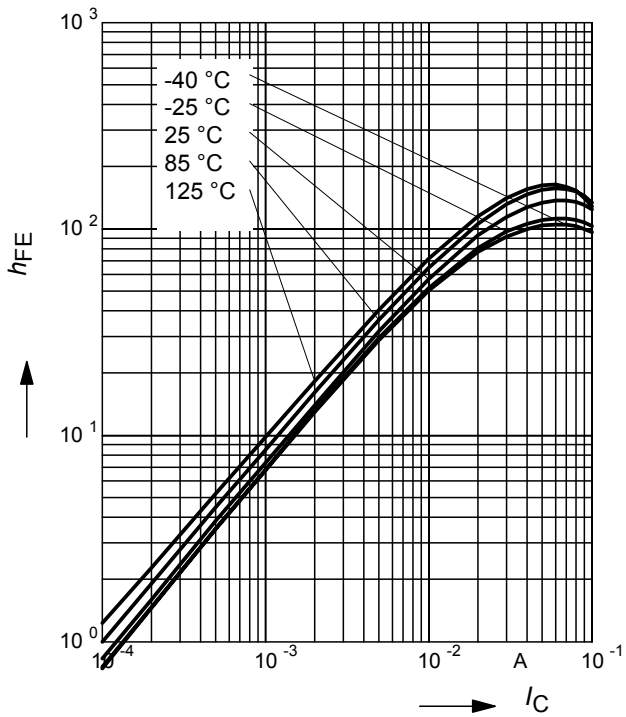
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	f_T	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{cb}	-	3	-	pF

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

²Pulse test: $t < 300 \mu\text{s}; D < 2\%$

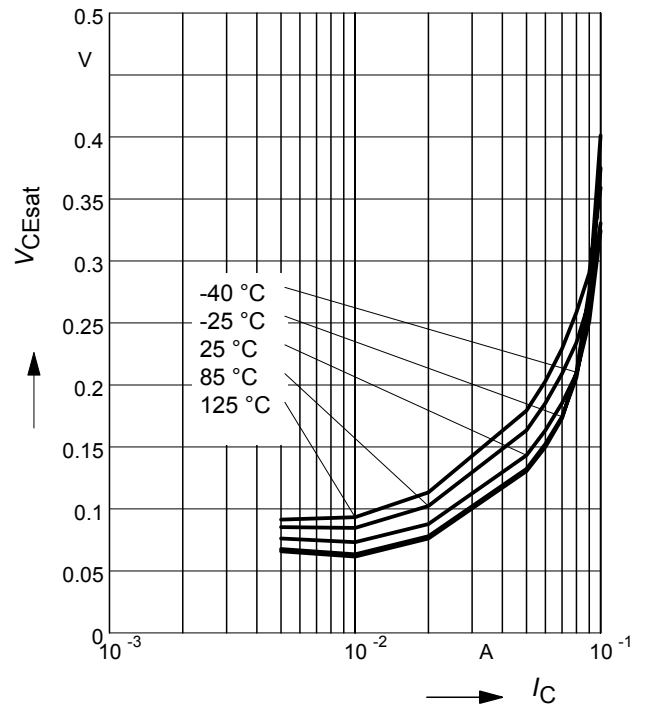
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5\text{ V}$ (common emitter configuration)



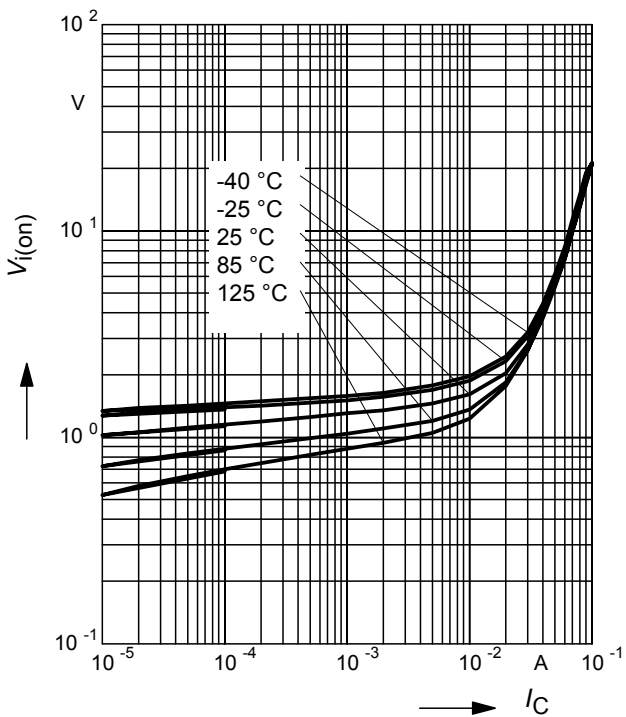
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C), I_C/I_B = 20$



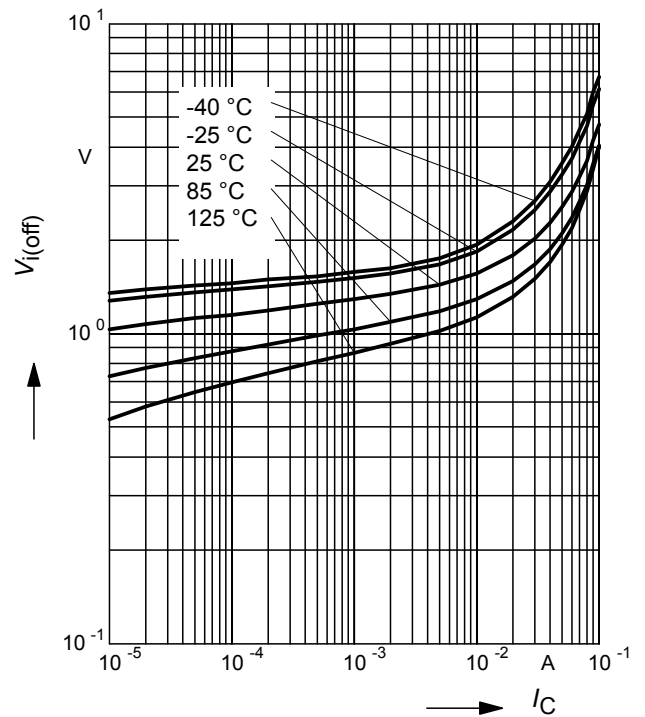
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3\text{V}$ (common emitter configuration)



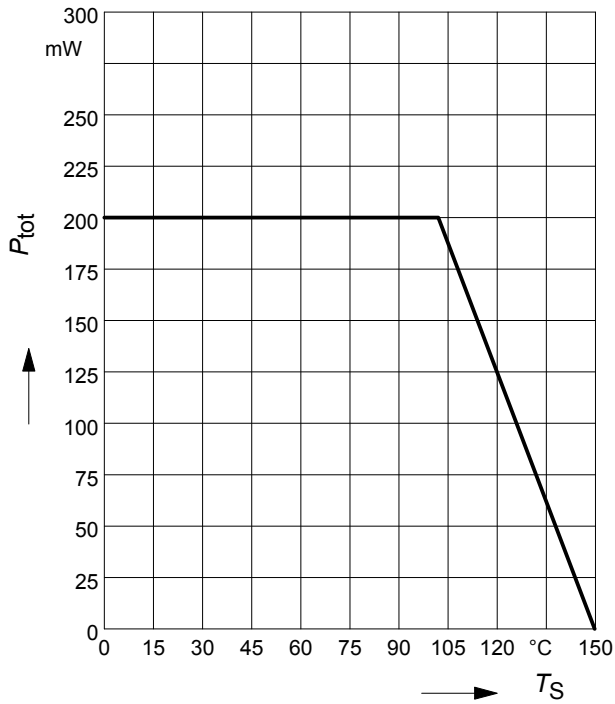
Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5\text{V}$ (common emitter configuration)



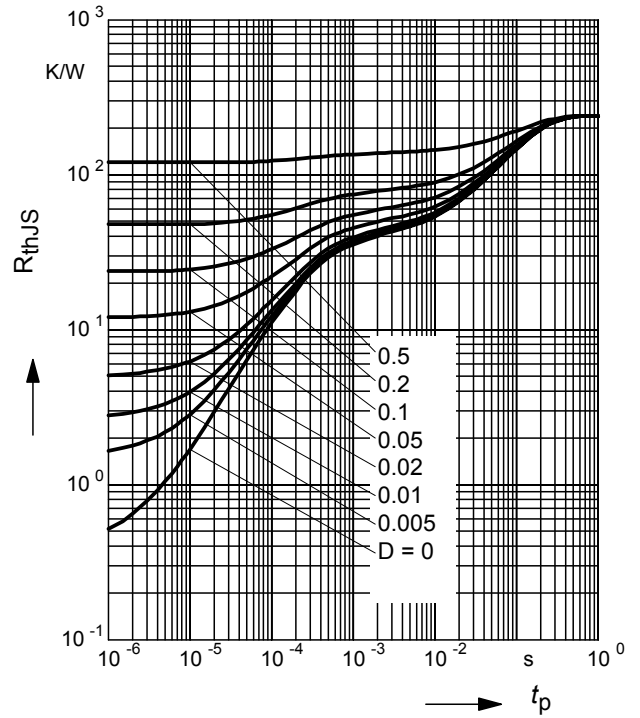
Total power dissipation $P_{tot} = f(T_S)$

BCR162



Permissible Pulse Load $R_{thJS} = f(t_p)$

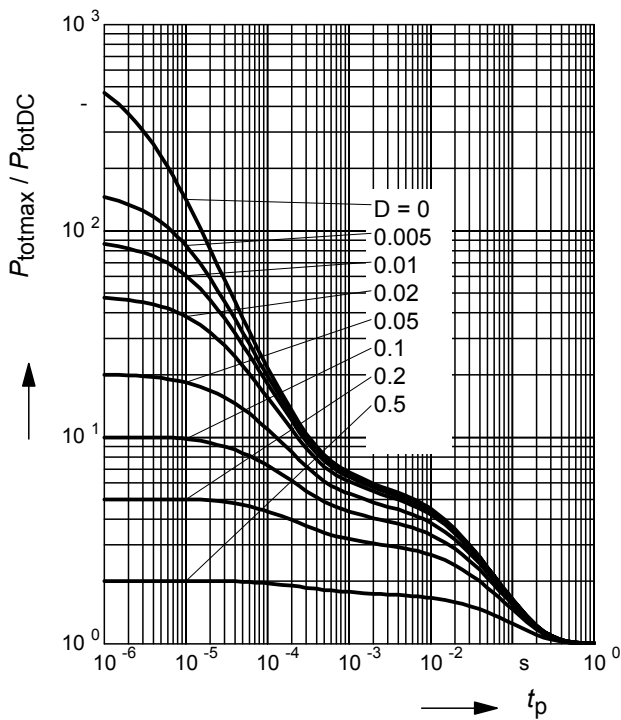
BCR162



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

BCR162



Package Outline



1) Lead width can be 0.6 max. in dambar area

Foot Print



Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



Edition 2009-11-16

**Published by
Infineon Technologies AG
81726 Munich, Germany**

**© 2009 Infineon Technologies AG
All Rights Reserved.**

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - Pre-Biased](#) category:

Click to view products by [Infineon](#) manufacturer:

Other Similar products are found below :

[RN1607\(TE85L,F\)](#) [DTA124GKAT146](#) [DTA144WETL](#) [DTA144WKAT146](#) [DTC113EET1G](#) [DTC115TETL](#) [DTC115TKAT146](#)
[DTC124TETL](#) [DTC144ECA-TP](#) [DTC144VUAT106](#) [MUN5241T1G](#) [NSBA114TDP6T5G](#) [NSBA143ZF3T5G](#) [NSBC114YF3T5G](#)
[NSBC123TF3T5G](#) [SMUN5235T1G](#) [SMUN5330DW1T1G](#) [SSVMUN5312DW1T2G](#) [RN1303\(TE85L,F\)](#) [RN4605\(TE85L,F\)](#)
[TTEPROTOTYPE79](#) [DDTC114EUAQ-7-F](#) [EMH15T2R](#) [SMUN2214T3G](#) [NSBC114TF3T5G](#) [NSBC143ZPDP6T5G](#)
[NSVMUN5113DW1T3G](#) [SMUN5230DW1T1G](#) [SMUN5133T1G](#) [SMUN2214T1G](#) [DTC114EUA-TP](#) [NSBA144EF3T5G](#)
[NSVDTA114EET1G](#) [2SC2223-T1B-A](#) [2SC3912-TB-E](#) [SMUN5237DW1T1G](#) [SMUN5213DW1T1G](#) [SMUN5114DW1T1G](#) [SMUN2111T1G](#)
[NSVDTC144EM3T5G](#) [DTC124ECA-TP](#) [DTC123TM3T5G](#) [DTA114ECA-TP](#) [DTA113EM3T5G](#) [DCX115EK-7-F](#) [DTC113EM3T5G](#)
[NSVMUN5135DW1T1G](#) [NSVDTC143ZM3T5G](#) [SMUN5216DW1T1G](#) [NSVMUN5312DW1T2G](#)